



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



Silicon Carbide Power Schottky Diode

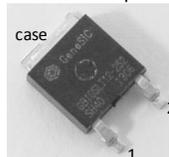
V_{RRM}	=	1200 V
$I_F (T_C = 25^\circ\text{C})$	=	25 A
$I_F (T_C \leq 150^\circ\text{C})$	=	10 A
Q_C	=	31 nC

Features

- Industry's leading low leakage currents
- 175 °C maximum operating temperature
- Temperature independent switching behavior
- Superior surge current capability
- Positive temperature coefficient of V_F
- Extremely fast switching speeds
- Superior figure of merit Q_C/I_F

Package

- RoHS Compliant


TO – 252


Advantages

- Low standby power losses
- Improved circuit efficiency (Lower overall cost)
- Low switching losses
- Ease of paralleling devices without thermal runaway
- Smaller heat sink requirements
- Low reverse recovery current
- Low device capacitance
- Low reverse leakage current at operating temperature

Applications

- Power Factor Correction (PFC)
- Switched-Mode Power Supply (SMPS)
- Solar Inverters
- Wind Turbine Inverters
- Motor Drives
- Induction Heating
- Uninterruptible Power Supply (UPS)
- High Voltage Multipliers

Maximum Ratings at $T_j = 175^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Repetitive peak reverse voltage	V_{RRM}			1200		V
Continuous forward current	I_F	$T_C = 25^\circ\text{C}$		25		A
Continuous forward current	I_F	$T_C \leq 150^\circ\text{C}$		10		A
RMS forward current	$I_{F(RMS)}$	$T_C \leq 150^\circ\text{C}$		17		A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25^\circ\text{C}, t_p = 10\text{ ms}$		65		A
		$T_C = 150^\circ\text{C}, t_p = 10\text{ ms}$		55		A
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25^\circ\text{C}, t_p = 10\text{ }\mu\text{s}$		280		A
I^2t value	$\int i^2 dt$	$T_C = 25^\circ\text{C}, t_p = 10\text{ ms}$		21		A ² s
		$T_C = 150^\circ\text{C}, t_p = 10\text{ ms}$		15		A ² s
Power dissipation	P_{tot}	$T_C = 25^\circ\text{C}$		190		W
Operating and storage temperature	T_j, T_{stg}			-55 to 175		°C

Electrical Characteristics at $T_j = 175^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Diode forward voltage	V_F	$I_F = 10\text{ A}, T_j = 25^\circ\text{C}$		1.5	1.8	V
		$I_F = 10\text{ A}, T_j = 175^\circ\text{C}$		2.6	3.0	
Reverse current	I_R	$V_R = 1200\text{ V}, T_j = 25^\circ\text{C}$		50	250	μA
		$V_R = 1200\text{ V}, T_j = 175^\circ\text{C}$		100	500	
Total capacitive charge	Q_C	$I_F \leq I_{F,MAX}$ $dI_F/dt = 200\text{ A}/\mu\text{s}$ $T_j = 175^\circ\text{C}$	$V_R = 400\text{ V}$	31		nC
	$V_R = 960\text{ V}$		52			
Switching time	t_s	$V_R = 1\text{ V}, f = 1\text{ MHz}, T_j = 25^\circ\text{C}$	$V_R = 400\text{ V}$	< 25		ns
			$V_R = 960\text{ V}$			
Total capacitance	C	$V_R = 1\text{ V}, f = 1\text{ MHz}, T_j = 25^\circ\text{C}$		490		pF
		$V_R = 400\text{ V}, f = 1\text{ MHz}, T_j = 25^\circ\text{C}$		45		
		$V_R = 1000\text{ V}, f = 1\text{ MHz}, T_j = 25^\circ\text{C}$		33		

Thermal Characteristics

Thermal resistance, junction - case	R_{thJC}	0.8	°C/W
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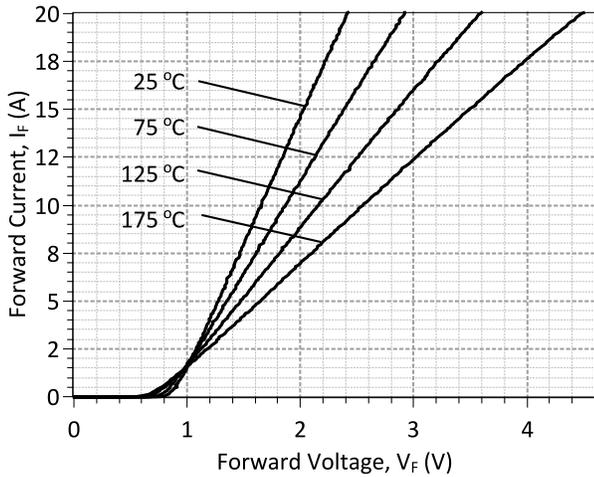


Figure 1: Typical Forward Characteristics

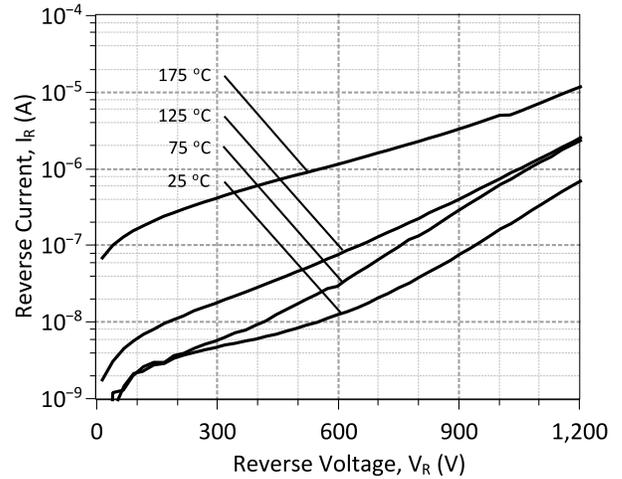


Figure 2: Typical Reverse Characteristics

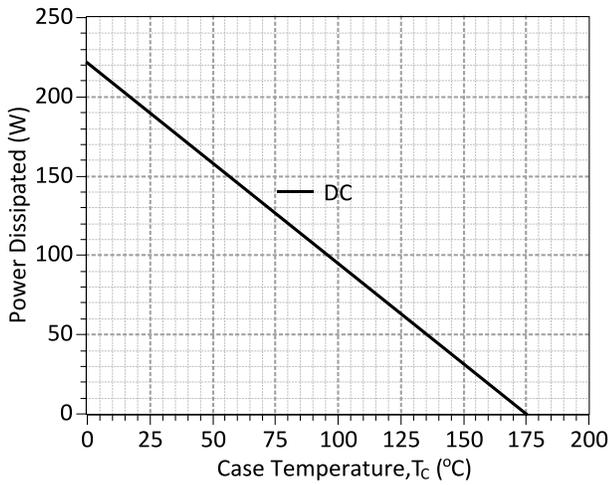
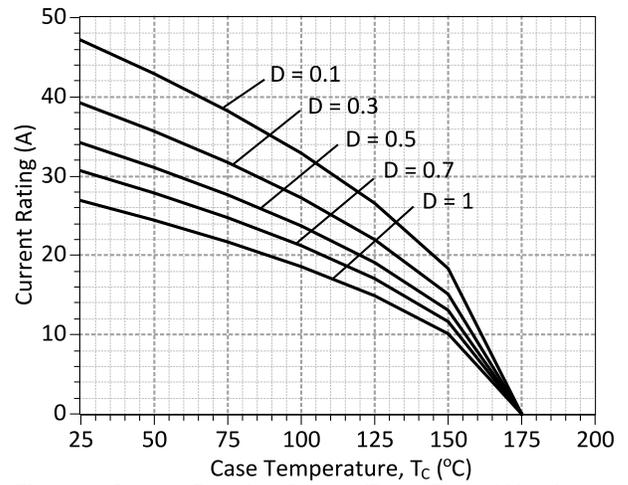


Figure 3: Power Derating Curve



**Figure 4: Current Derating Curves (D = t_p/T , $t_p = 400 \mu s$)
(Considering worst case Z_{th} conditions)**

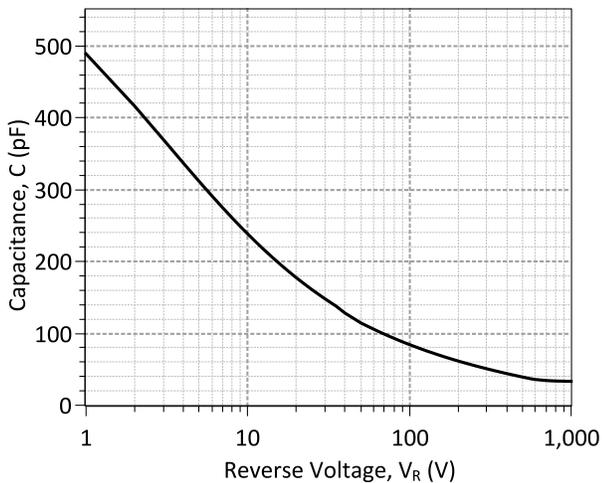


Figure 5: Typical Junction Capacitance vs Reverse Voltage Characteristics

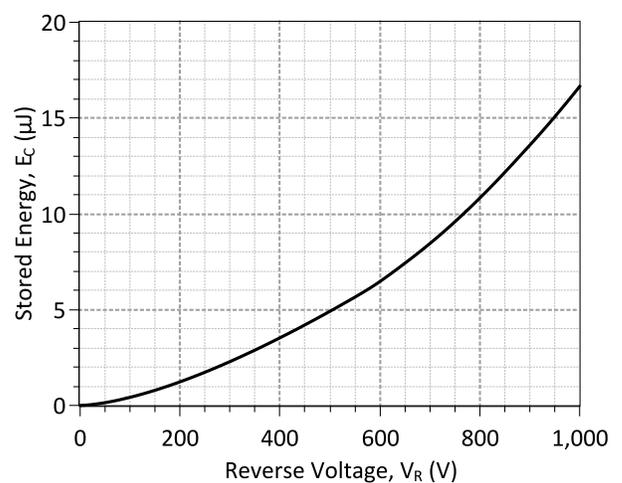


Figure 6: Typical Capacitive Energy vs Reverse Voltage Characteristics

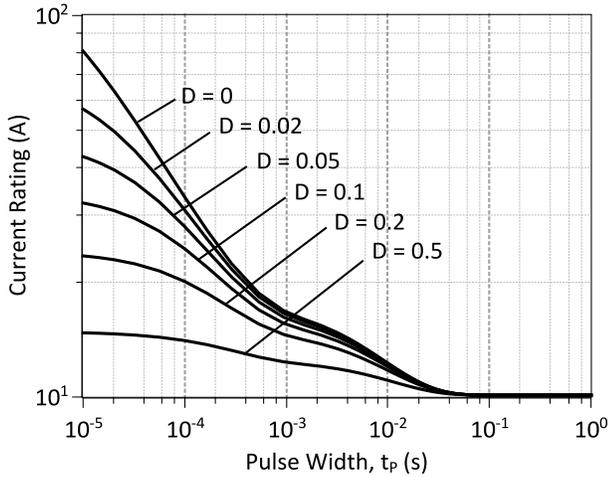


Figure 7: Current vs Pulse Duration Curves at $T_c = 150\text{ }^\circ\text{C}$

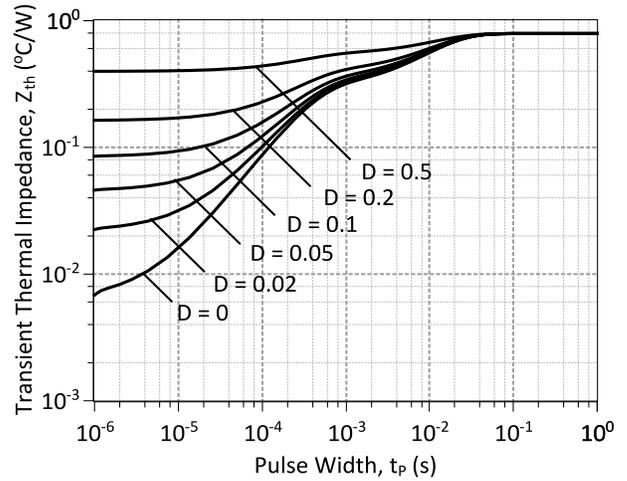
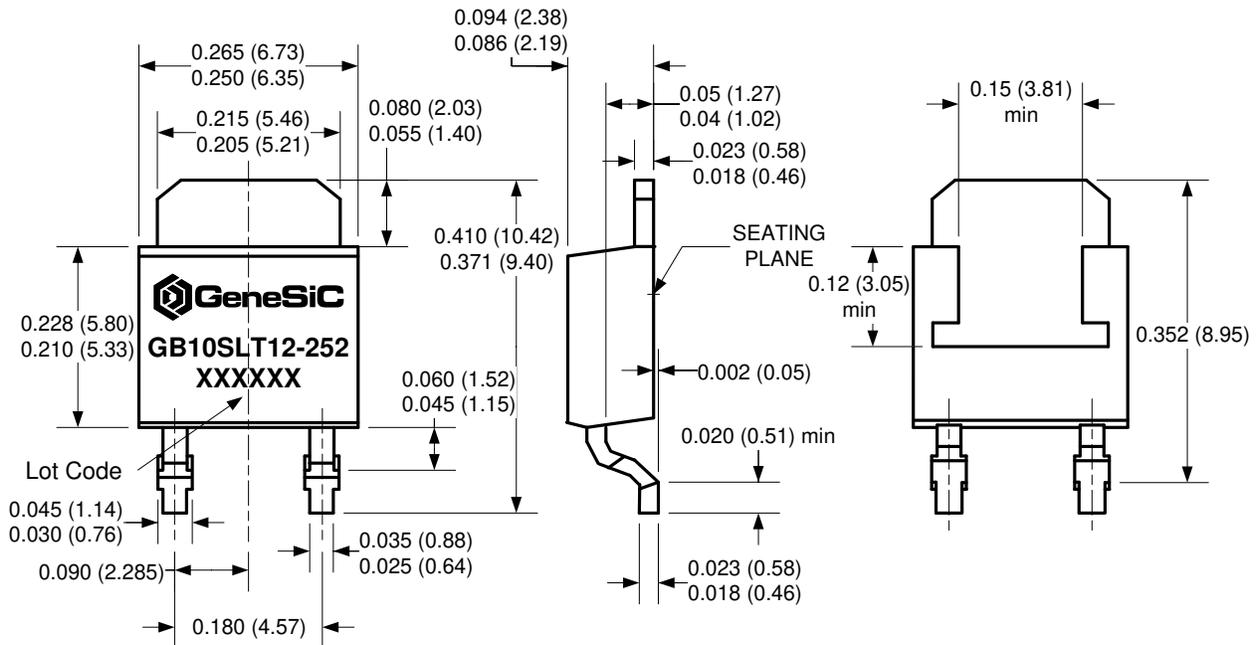


Figure 8: Transient Thermal Impedance

Package Dimensions:

TO-252

PACKAGE OUTLINE



NOTE

1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS

Revision History

Date	Revision	Comments	Supersedes
2014/08/26	4	Updated Electrical Characteristics	
2013/06/12	3	Updated Electrical Characteristics	
2012/12/18	2	Second generation update	
2012/05/22	1	Second generation release	
2010/12/14	0	Initial release	

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43670 Trade Center Place Suite 155
Dulles, VA 20166

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SPICE Model Parameters

This is a secure document. Please copy this code from the SPICE model PDF file on our website (http://www.genesicsemi.com/images/products_sic/rectifiers/GB10SLT12-252_SPICE.pdf) into LTSPICE (version 4) software for simulation of the GB10SLT12-252.

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*      MODEL OF GeneSiC Semiconductor Inc.
*
*      $Revision:   1.0           $
*      $Date:      04-SEP-2013   $
*
*      GeneSiC Semiconductor Inc.
*      43670 Trade Center Place Ste. 155
*      Dulles, VA 20166
*
*      COPYRIGHT (C) 2013 GeneSiC Semiconductor Inc.
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*
*      These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
*      OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
*      TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
*      PARTICULAR PURPOSE."
*      Models accurate up to 2 times rated drain current.
*
*      Start of GB10SLT12-252 SPICE Model
*
.SUBCKT GB10SLT12 ANODE KATHODE
D1 ANODE KATHODE GB10SLT12_SCHOTTKY
D2 ANODE KATHODE GB10SLT12_PIN
.MODEL GB10SLT12_SCHOTTKY D
+ IS      4.55E-15      RS      0.0736
+ N       1            IKF     1000
+ EG      1.2          XTI     -2
+ TRS1    0.0054347826 TRS2    2.71739E-05
+ CJO     6.40E-10     VJ      0.469
+ M       1.508        FC      0.5
+ TT      1.00E-10     BV      1200
+ IBV     1.00E-03     VPK     1200
+ IAVE    10          TYPE     SiC_Schottky
+ MFG     GeneSiC_Semi
.MODEL GB10SLT12_PIN D
+ IS      1.54E-22     RS      0.19
+ TRS1    -0.004      N       3.941
+ EG      3.23        IKF     19
+ XTI     0           FC      0.5
+ TT      0           BV      1200
+ IBV     1.00E-03     VPK     1200
+ IAVE    10          TYPE     SiC_PiN
.ENDS
*
*      End of GB10SLT12-252 SPICE Model
```